## Abstract Submitted for the 4CF15 Meeting of The American Physical Society

Contribution of Lifshitz-Van der Waals Interactions to the Surface Energy  $\gamma^T$  of Si(100)-based Surfaces using the Van Oss-Young-Dupre Model ALEX L. BRIMHALL, ASHLEY A. MASCARENO, ENDER W. DAVIS, Arizona State University Dpt. Physics, MATTHEW T. BADE, Arizona State University Dpt. Physics/Brophy College Preparatory, NITHIN KANNAN, ABIJITH KRISHNAN, Arizona State University Dpt. Physics/BASIS Scottsdale HS, NICOLE HERBOTS, Arizona State University Dpt. Physics, CLARIZZA F. WATSON, SiO2 Nanotech LLC, SIO2 NANOTECH LLC TEAM — Surface energy  $\gamma^T$  is studied via 3 Liquid Contact Angle Analysis (3LCAA) to optimize Wet NanoBonding<sup>TM</sup>, where surfaces hermetically cross-bond by anneal < 200°C. Applications lie in electronic sensors in saline environments. The Van Oss theory models interactions with dipoles (Lifshitz-Van der Waals)  $\gamma^{LW}$ , electron donors  $\gamma^+$ , and acceptors  $\gamma^{-}$ . Combining the equations of Van Oss and Young-Dupre yield the total  $\gamma^T$  and its 3 components. Contact angles for 3 different liquids are measured with the sessile drop method on 4-8 drops per liquid for accuracy, in a Class 100 hood. Si wafers are studied after RCA clean or Herbots-Atluri (H-A) processing. After H-A, 2 sets are treated with Rapid Thermal Anneal or Oxidation (RTA or RTO).  $\gamma^{T}$  is higher for the more defective, hydrophilic RCA cleaned Si  $(47.3 \pm 0.5 \frac{mJ}{m^2})$ , while it is lower for the more ordered, hydrophobic H-A surfaces  $(37.3 \pm 1.5 \frac{mJ}{m^2})$  and RTO  $(34.5 \pm 0.5 \frac{mJ}{m^2})$ . In addition,  $\gamma^{LW}$  interactions account for 90 to 98% of  $\gamma^T$  in ordered oxides, unlike in hydrophilic surfaces (76.5%). This indicates that 3LCAA can detect decreases in surface interaction from surface defects, impurities, and dangling bonds.

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